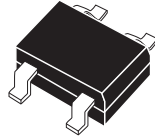


**CBR1-D020S SERIES**  
**SURFACE MOUNT**  
**1 AMP DUAL IN LINE**  
**SILICON BRIDGE RECTIFIER**



**SMDIP CASE**

# Central<sup>TM</sup>

**Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CBR1-D020S series types are silicon full wave bridge rectifiers mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips.

NOTE: Also available in Fast Recovery, please contact factory for details.

**MARKING CODE: FULL PART NUMBER**

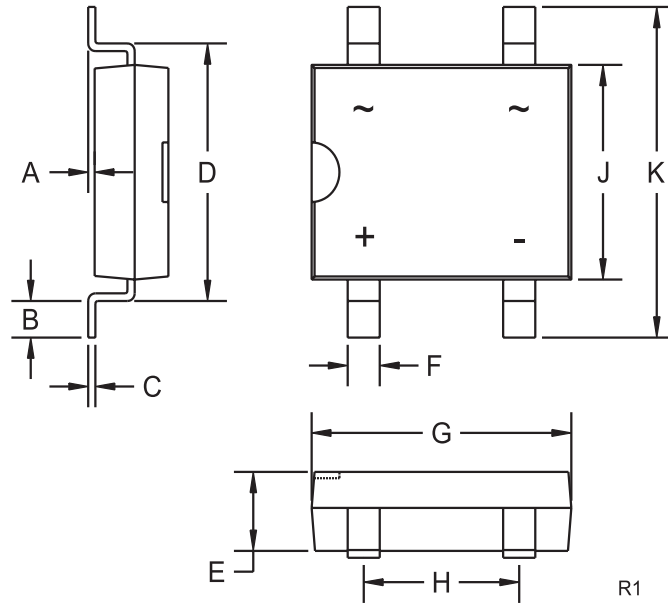
**MAXIMUM RATINGS** ( $T_A=25^{\circ}\text{C}$ )

	SYMBOL	CBR1-D020S	CBR1-D040S	CBR1-D060S	CBR1-D080S	CBR1-D100S	UNITS
Peak Repetitive Reverse Voltage	$V_{RRM}$	200	400	600	800	1000	V
DC Blocking Voltage	$V_R$	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	140	280	420	560	700	V
Average Forward Current ( $T_A=50^{\circ}\text{C}$ )	$I_O$			1.0			A
Peak Forward Surge Current	$I_{FSM}$			50			A
Rating for Fusing ( $t<8.35\text{ms}$ )	$I^2t$			10			A <sup>2</sup> s
Operating and Storage							
Junction Temperature	$T_J, T_{stg}$			-65 to +150			$^{\circ}\text{C}$

**ELECTRICAL CHARACTERISTICS** ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_R$	$V_R=\text{Rated } V_{RRM}$			10	$\mu\text{A}$
$I_R$	$V_R=\text{Rated } V_{RRM}, T_A=125^{\circ}\text{C}$			0.5	mA
$V_F$	$I_F=1.0\text{A}$			1.1	V
$C_J$	$V_R=4.0\text{V}, f=1.0\text{MHz}$		25		pF

SMDIP CASE - MECHANICAL OUTLINE



MARKING CODE:  
FULL PART NUMBER

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.008	0.10	0.20
B	0.040	0.060	1.02	1.52
C	0.009		0.23	
D	0.290	0.310	7.37	7.87
E	0.086	0.098	2.18	2.49
F	0.038	0.042	0.97	1.07
G	0.316	0.335	8.03	8.51
H	0.195	0.205	4.95	5.21
J	0.245	0.255	6.22	6.48
K	0.360	0.410	9.14	10.41

SMDIP (REV: R1)